

## AMENDMENTS TO THE CLAIMS

This listing of claim will replace all prior versions and listings of claim in the application.

1. – 51. (Cancelled).

52. (New) A non-volatile memory system, comprising:

a card having a set of contacts on an external surface of said card, said card having a first surface and a second surface on an opposite side of said card from said first surface, said first surface having a raised portion;

a circuit board enclosed within said card;

a plurality of non-volatile storage elements enclosed within said card and connected to said circuit board; and

passive electrical elements enclosed within said card and connected to said circuit board, said passive electrical elements are positioned in a part of said card at least partially defined by said raised portion.

53. (New) A non-volatile memory system according to claim 52, wherein:  
said non-volatile storage elements are flash memory cells.

54. (New) A non-volatile memory system according to claim 52, wherein:  
said first surface defines a length and a width of said card.

55. (New) A non-volatile memory system according to claim 52, further comprising:  
a controller element enclosed within said card and connected to said circuit board.

56. (New) A non-volatile memory system according to claim 55, wherein:  
said passive electrical elements are in communication with said controller.

57. (New) A non-volatile memory system according to claim 52, wherein:  
said first surface is a top surface of said card.
58. (New) A non-volatile memory system according to claim 52, wherein:  
said passive electrical elements are capacitors.
59. (New) A non-volatile memory system according to claim 52, further comprising:  
side surfaces between said first surface and said second surface.
60. (New) A non-volatile memory system according to claim 52, wherein:  
said raised portion provides a grip to grab said card.
61. (New) A non-volatile memory system according to claim 52, wherein:  
said card includes molding material encapsulating said circuit board, said non-volatile storage  
elements and said passive electrical elements.
62. (New) A non-volatile memory system according to claim 52, wherein:  
said non-volatile storage elements are flash memory devices in a flash memory array; and  
said passive electrical elements are capacitors.
63. (New) A non-volatile memory system, comprising:  
a card having a first dimension and a second dimension, said card has a first thickness along a  
first portion of said first dimensions and a second thickness along a second portion of said first  
dimension, said second thickness is greater than said first thickness;  
a plurality of non-volatile storage elements enclosed within said card; and  
passive electrical elements enclosed within said card, said passive electrical elements are  
positioned in said second portion.

64. (New) A non-volatile memory system according to claim 63, wherein:  
said passive electrical elements are capacitors.
65. (New) A non-volatile memory system according to claim 64, wherein:  
said first dimension is length;  
said second dimension is width; and  
said non-volatile storage elements are flash memory devices.
66. (New) A non-volatile memory system according to claim 63, wherein:  
said first dimension is length; and  
said second dimension is width.
67. (New) A non-volatile memory system according to claim 63, wherein:  
said passive electrical elements are in electrical communication with said non-volatile storage elements.
68. (New) A non-volatile memory system according to claim 63, further comprising:  
a circuit board, said non-volatile storage elements and said passive electrical elements are connected to said circuit board.
69. (New) A non-volatile memory system according to claim 68, further comprising:  
a controller, said controller is positioned within said card and is in communication with said non-volatile storage elements; and  
a set of electrical contacts on an external surface of said card, said set of electrical contacts are in communication with said controller.
70. (New) A non-volatile memory system according to claim 63, wherein:  
said non-volatile storage elements are flash memory devices.

71. (New) A non-volatile memory system according to claim 63, further comprising:  
a controller element enclosed within said card and in communication with said non-volatile storage elements.

72. (New) A non-volatile memory system according to claim 63, wherein:  
said card having a first surface and a second surface on an opposite side of said card from said first surface, said first surface having a raised portion, said raised portion defines said second thickness.

73. (New) A non-volatile memory system according to claim 63, wherein:  
said card includes molding material encapsulating said plurality of non-volatile storage elements and said passive electrical elements.

74. (New) A method of making a memory system, comprising:  
adding non-volatile storage elements to a circuit;  
adding passive electrical components to said circuit; and  
encapsulating said circuit, including said non-volatile storage elements and said passive electrical components, to form a memory card having a first dimension and a second dimension,  
said memory card has a first thickness along a first portion of said first dimensions and a second thickness along a second portion of said first dimension, said second thickness is greater than said first thickness, said passive electrical components are positioned in said second portion.

75. (New) A method according to claim 74, further comprising:  
adding a controller to said circuit prior to said step of encapsulating.

76. (New) A method according to claim 75, further comprising:  
adding a first set of electrical contacts to an external surface of said memory card, said first

set of electrical contacts are in communication with said controller.

77. (New) A method according to claim 74, wherein:  
said passive electrical components include capacitors.

78. (New) A method according to claim 74, wherein:  
said non-volatile storage elements are flash memory devices.

79. (New) A method according to claim 74, wherein:  
said card has a first surface and a second surface on an opposite side of said card from said first surface, said first surface includes a raised portion, said passive electrical components are positioned in an area of said card at least partially defined by said raised portion.

80. (New) A non-volatile memory system, comprising:  
a peripheral card having a first dimension and a second dimension, said card has a first thickness along a first portion of said first dimensions and a second thickness along a second portion of said first dimension, said second thickness is greater than said first thickness;  
non-volatile storage elements enclosed within said peripheral card; and  
a passive electrical component enclosed within said peripheral card, said passive electrical element is positioned in said second portion.

81. (New) A non-volatile memory system, comprising:  
a peripheral card having a first surface and a second surface on an opposite side of said card from said first surface, said first surface having a raised portion;  
a circuit board enclosed within said peripheral card;  
a plurality of non-volatile storage elements enclosed within said peripheral card and connected to said circuit board; and

a passive electrical component enclosed within said peripheral card and connected to said circuit board, said passive electrical component is positioned in a part of said card at least partially defined by said raised portion.